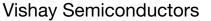
www.vishay.com



Ultrafast Rectifier, 8 A FRED Pt[®]



Bas catho	
	• 3
Cathode	Anode

TO-220AC

PRODUCT SUMMARY									
Package	TO-220AC								
I _{F(AV)}	8 A								
V _R	200 V								
V_F at I_F	0.895 V								
t _{rr} typ.	See Recovery table								
T _J max.	175 °C								
Diode variation	Single die								

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Designed and qualified according JEDEC®-JESD 47



COMPLIANT HALOGEN FREE to

 Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

VS-MUR820PbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time guarantee the best overall performance, control, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS					
Peak repetitive reverse voltage	V _{RRM}		200	V					
Average rectified forward current	I _{F(AV)}	Total device, rated V_R , $T_C = 150 \ ^\circ C$	8						
Non-repetitive peak surge current	I _{FSM}		100	А					
Peak repetitive forward current	I _{FM}	Rated V _R , square wave, 20 kHz, $T_C = 150 \text{ °C}$	16						
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C					

ELECTRICAL SPECIFICATIONS ($T_J = 25 \ ^{\circ}C$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-				
Forward voltage	V _F	I _F = 8 A	-	-	0.975	V			
		I _F = 8 A, T _J = 150 °C	-	-	0.895				
Reverse leakage current	I _R	$V_{R} = V_{R}$ rated	-	-	5				
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$		250	μA				
Junction capacitance	CT	V _R = 200 V	-	25	-	pF			
Series inductance	Ls	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

Revision: 10-Jul-15 Document Number: 94523 1 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishav.com/doc?91000



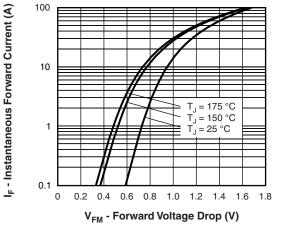
www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V _R = 30 V	-	-	35				
	+	$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ A}$		-	-	25	20			
	t _{rr}	T _J = 25 °C		-	20	-	ns			
		T _J = 125 °C	$I_F = 8 A$	-	34	-				
Peak recovery current	I _{RRM}	T _J = 25 °C		-	1.7	-				
		T _J = 125 °C	dl _F /dt = 200 A/µs V _R = 160 V	-	4.2	-	A			
Reverse recovery charge	0	T _J = 25 °C		-	23	-	nC			
	Q _{rr}	T _J = 125 °C]	-	75	-				

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	3.0				
Thermal resistance, junction to ambient	R _{thJA}		-	-	50	°C/W			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-220AC		MUF	R820				

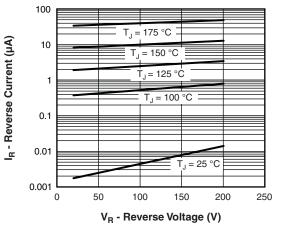
Vishay Semiconductors

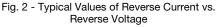


www.vishay.com

ISHAY

Fig. 1 - Maximum Forward Voltage Drop Characteristics





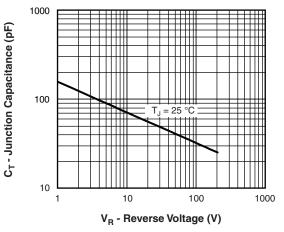


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

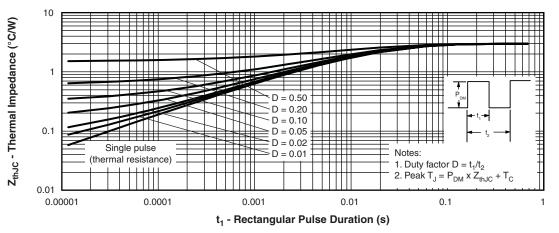


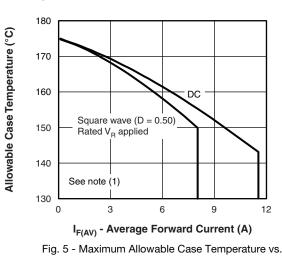
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

 Revision: 10-Jul-15
 3
 Document Number: 94523

 For technical questions within your region: DiodesAsia@vishay.com, DiodesEurope@vishay.com

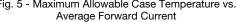
 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

Vishay Semiconductors



www.vishay.com

ISHAY



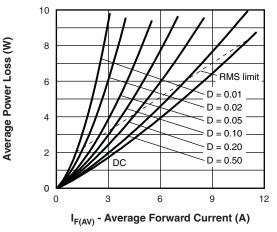
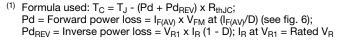


Fig. 6 - Forward Power Loss Characteristics

Note



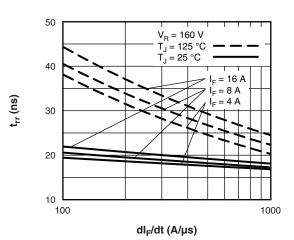


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

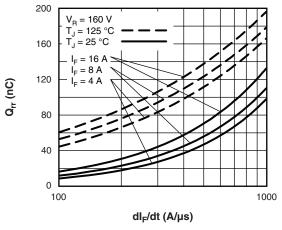


Fig. 8 - Typical Stored Charge vs. dl_F/dt

 Revision: 10-Jul-15
 4
 Document Number: 94523

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 DiodesEurope@vishay.com

 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



Downloaded from Arrow.com.

Vishay Semiconductors

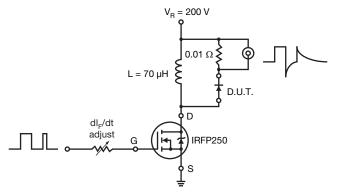


Fig. 9 - Reverse Recovery Parameter Test Circuit

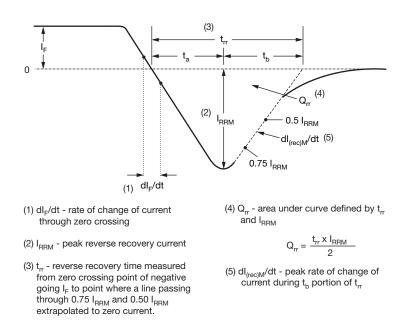


Fig. 10 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code	VS-	MUR	8	20	PbF	
	1	2	3	4	5	
	1 -		nay Sem			oduct
	2 - 3 -		afast MU rent ratir		-	
	4 -		age ratii	0 (,	1
	5 -		ironmen	0		
				. ,		oHS,compliant

-N3 = halogen-free, RoHS-compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-MUR820PbF	50	1000	Antistatic plastic tube					
VS-MUR820-N3	50	1000	Antistatic plastic tube					

LINKS TO RELATED DOCUMENTS								
Dimensions		www.vishay.com/doc?95221						
Part marking information	TO-220ACPbF	www.vishay.com/doc?95224						
	TO-220AC-N3	www.vishay.com/doc?95068						



Vishay Semiconductors

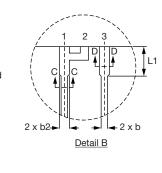
TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

SYMBOL	MILLIM	IETERS	INC	HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183		E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055		E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115		е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040		e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4	H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068		L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4	L1	3.32	3.82	0.131	0.150	2
С	0.36	0.61	0.014	0.024		L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4	L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3	ØΡ	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355		Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6	θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6						

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline

Document Number: 95221 Revision: 07-Mar-11



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.